A REVOLUTIONARY BREAKTHROUGH IN MEMORY TECHNOLOGY



SAFE HARBOR

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A TIMELINE OF MEMORY CLASS INTRODUCTIONS

Ram



PA28F800 B5T70 U82604888 E 00092'95



IT'S BEEN DECADES SINCE THE LAST MAINSTREAM MEMORY

THE EXPLOSION OF MODERN DATA

REQUIRES

A REVOLUTIONARY NEW TECHNOLOGY

CAPACITY

PERFORMANCE

NON-VOLATILE

THE BREAKTHROUGH A NEW CLASS OF NON-VOLATILE MEMORY

1000X FASTER THAN NAND

1000X ENDURANCE OF NAND

10X DENSER THAN CONVENTIONAL MEMORY

*Results have been estimated or simulated using internal analysis or architecture simulation or modeling, and provided to you for informational purposes. Any differences in your system hardware, software or configuration may affect your actual performance

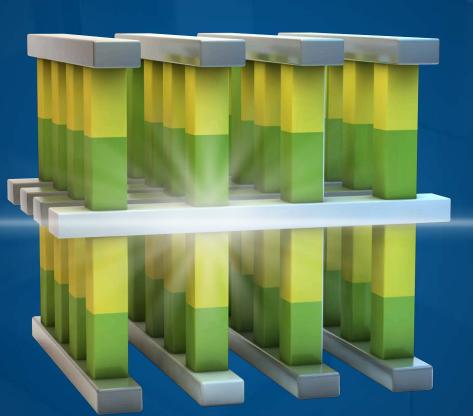
WHAT IS 3D XPOINT™?

Crosspoint Structure

Selectors allow dense packing and individual access to bits

Scalable

Memory layers can be stacked in a 3D manner



Breakthrough Material Advances

Compatible switch and memory cell materials

High Performance

Cell and array architecture that can switch states 1000x faster than NAND

3D XPOINT™ ENABLES FUTURE APPLICATIONS

END USER POSSIBILITIES



Massive in-memory data base



Fast system recovery



Low latency



High endurance



Gaming



High fidelity pattern recognition



Genomics

AMAZING NEW EXPERIENCES



A REVOLUTIONARY BREAKTHROUGH IN MEMORY TECHNOLOGY

